

CLAIMS

What is claimed is:

1. A customized polishing pad adapted for use in a wafer polishing machine, said customized polishing pad comprising:

a polishing pad adapted for use in a wafer polishing machine;

a polishing surface included in said polishing pad, said polishing surface adapted to frictionally contact a wafer in said wafer polishing machine;

a first region integral with said polishing surface, said first region adapted to frictionally contact said wafer, said first region adapted to achieve a first process effect; and

a second region integral with said polishing surface, said second region adapted to frictionally contact said wafer, said second region adapted to achieve a second process effect such that said wafer polishing machine achieves a customized process effect by selectively moving said wafer frictionally against said first region and said second region.

2. The customized polishing pad of claim 1 further comprising:

a first underlying layer included in said polishing pad, said first underlying layer adapted to achieve said first polishing effect in said first region; and

a second underlying layer included in said polishing pad, said second underlying layer adapted to achieve said second polishing effect in said second process effect in said second region.

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How if they are lawyers?

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Year	1980	1981	1982	1983	1984	1985	1986	1987	1988	1989	1990	1991	1992	1993	1994	1995	1996	1997	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034	2035	2036	2037	2038	2039	2040	2041	2042	2043	2044	2045	2046	2047	2048	2049	2050	2051	2052	2053	2054	2055	2056	2057	2058	2059	2060	2061	2062	2063	2064	2065	2066	2067	2068	2069	2070	2071	2072	2073	2074	2075	2076	2077	2078	2079	2080	2081	2082	2083	2084	2085	2086	2087	2088	2089	2090	2091	2092	2093	2094	2095	2096	2097	2098	2099	2100
1980	1980	1981	1982	1983	1984	1985	1986	1987	1988	1989	1990	1991	1992	1993	1994	1995	1996	1997	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034	2035	2036	2037	2038	2039	2040	2041	2042	2043	2044	2045	2046	2047	2048	2049	2050	2051	2052	2053	2054	2055	2056	2057	2058	2059	2060	2061	2062	2063	2064	2065	2066	2067	2068	2069	2070	2071	2072	2073	2074	2075	2076	2077	2078	2079	2080	2081	2082	2083	2084	2085	2086	2087	2088	2089	2090	2091	2092	2093	2094	2095	2096	2097	2098	2099	2100

9. The customized polishing pad of claim 2 wherein said polishing pad is a linear polishing pad and said first region and said second region are linearly adjacent within said linear polishing pad.

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10. A multi-region polishing pad adapted for use in a wafer polishing machine, said multi-region polishing pad comprising:

a polishing pad adapted for use in a wafer polishing machine;

10 a polishing surface included in said polishing pad, said polishing surface adapted to frictionally contact a wafer in said wafer polishing machine;

15 a plurality of regions integral with said polishing surface, said plurality of regions each adapted to frictionally contact said wafer, each of said plurality of regions adapted to achieve a specific process effect such that said wafer polishing machine achieves a multi-region process effect by selectively moving said wafer frictionally against said plurality of regions.

11. The multi-region polishing pad of claim 10 further comprising:

20 a plurality of underlying layers included in said polishing pad, said plurality of underlying layers corresponding to said plurality of regions, each of said plurality of underlying layers adapted to achieve said specific process effect in said plurality of regions.

25 12. The multi-region polishing pad of claim 11 wherein each of said plurality of underlying layers have differing amounts of hardness when said wafer is frictionally moved against said polishing pad by said wafer polishing machine.

13. The multi-region polishing pad of claim 11 wherein said plurality of underlying layers form said polishing surface of said polishing pad.

14. The multi-region polishing pad of claim 11 further comprising: an overlying layer included in said polishing pad, said overlying layer forming said polishing surface, and said overlying layer coupled to each of said plurality of underlying layers.

15. The multi-region polishing pad of claim 14 wherein said polishing surface included in said overlying layer includes a plurality of textures, each of said plurality of textures adapted to achieve said specific process effect.

16. The multi-region polishing pad of claim 11 wherein said polishing pad is a circular polishing pad and said plurality of regions are concentrically adjacent within said circular polishing pad.

17. The multi-region polishing pad of claim 11 wherein said polishing pad is a linear polishing pad and said plurality of regions are linearly adjacent within said linear polishing pad.

18. In a chemical mechanical polishing (CMP) machine, a method of polishing a wafer, the method comprising the steps of:

a) placing a wafer onto a customized polishing pad on a chemical mechanical polishing machine, said polishing pad having a first region and a second region;

c) polishing said wafer using said second region by frictionally moving said wafer against said second region; and

19. The method of claim 18 further including the step of selectively polishing said wafer using said first region and said second region wherein said first region of said polishing pad is firmer than said second region of said polishing pad.

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